

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SMALL SIGNAL NPN TRANSISTOR WITH CONTROLLED BASE-EMITTER VOLTAGE

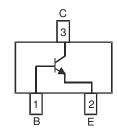
Features

- Low Deviation in Base-Emitter Voltage
- Surface Mount Package
- Ideally Suited for Automated Assembly Processes
- Lead Free by Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3 Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)





Schematic & Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	6	V
Output Current - Continuous (Note 3)	I _C	200	mA
Peak Collector Current	I _{CM}	200	mA
Peak Emitter Current	I _{EM}	200	mA
Power Dissipation (Note 3)	P _d	300	mW
Power Deration	P _{der}	2.4	mW/°C

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Ambient Air (Note 3)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Junction Temperature Range	T _j , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on page 4 or on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

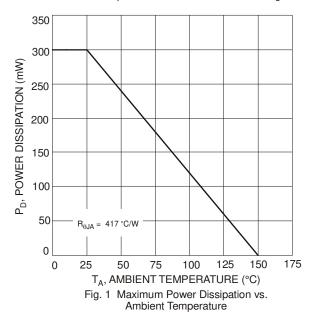
BC847BLD DS30824 Rev. 4 - 2 1 of 4 www.diodes.com

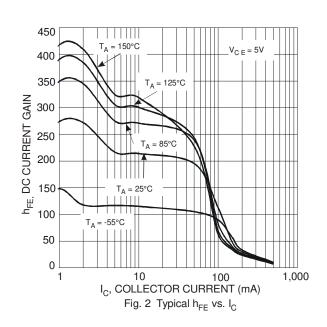


Electrical Characteristics: NPN Transistor @TA = 25°C unless otherwise specified

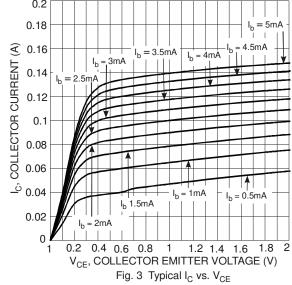
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	50	_	_	V	$I_C = 10 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	45	_	_	V	$I_C = 1.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6	_	_	V	$I_E = 10 \mu A, I_C = 0$
Collector Cutoff Current	I _{CEX}	_	_	15	nA	$V_{CE} = 50V, V_{EB(OFF)} = 3.0V$
Base Cutoff Current (I _{BEX})	I_{BL}	_	_	15	nA	$V_{CE} = 40V, V_{EB(OFF)} = 3.0V$
Collector-Base Cut Off Current	lana	_	_	15	nA	$V_{CB} = 40V, I_E = 0$
Collector-Base out on ourrent	I _{CBO}			5	μΑ	$V_{CB} = 30V, T_A = 150^{\circ}C$
Collector-Emitter Cut Off Current, I _{O(OFF)}	I _{CEO}	_	_	50	nA	$V_{CE} = 40V, I_B = 0$
Emitter-Base Cut Off Current	I _{EBO}	_	_	50	nA	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
	<u> </u>	180	_	_	_	$V_{CE} = 5V, I_{C} = 100 \mu A$
	<u>_</u>	150	_	_	_	$V_{CE} = 5V, I_{C} = 500 \mu A$
DC Current Gain	h _{fe}	220	_	_	_	$V_{CE} = 5V$, $I_C = 1mA$
Do dulicht dam	rite	220	_	_	_	$V_{CE} = 5V$, $I_C = 2mA$
		150	_	_	_	$V_{CE} = 5V$, $I_C = 5mA$
		150	_	_	_	$V_{CE} = 5V$, $I_C = 10mA$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.09	0.18	V	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$
Concetor Emitter Gaturation Voltage	V CE(SAT)		0.2	0.4	V	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
Base-Emitter Turn-On Voltage		647	657	667	mV	$V_{CE} = 5V$, $I_C = 2mA$
Base-Emitter Saturation Voltage		_	_	8.0	V	$I_C = 10mA, I_B = 0.5mA$
			_	0.9	V	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance		_	3	_	pF	$V_{CB} = 5.0V$, $f = 1.0 MHz$, $I_E = 0$
Input Impedance	h _{ie}		4.5	_	ΚΩ	
Voltage Feedback Ratio	h _{re}		2	_	x 10E-4	$V_{CE} = 5.0V$, $I_{C} = 2mA$,
Small Signal Current Gain	h _{fe}		200	_	_	f = 1.0KHz
Output Admittance	h _{oe}	_	30	_	μS	
Current Gain-Bandwidth Product	f _T	100	_	_	MHz	$V_{CE} = 20V, I_{C} = 10 \text{ mA},$ f = 100 MHz
Noise Figure	NF		_	10	dB	$V_{CE} = 5V$, $I_C = 100\mu A$, $R_S = 1K\Omega$, $f = 1kHz$

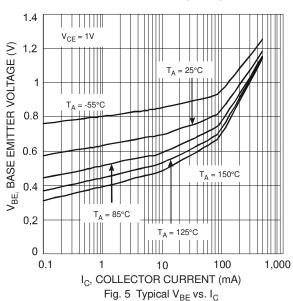
Notes: 4. Short duration pulse test used to minimize self-heating effect.

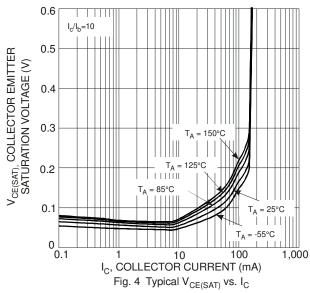


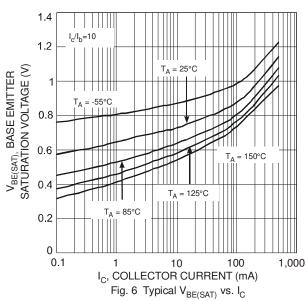










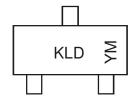


Ordering Information (Note 5)

Device	Packaging	Shipping
BC847BLD-7	SOT-23	3000/Tape & Reel

5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



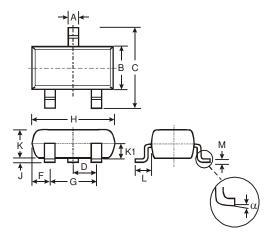
KLD = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2006	2007	20	800	2009	2010	2011	2012	2 20)13	2014	2015
Code	Т	U	,	V	W	Χ	Υ	Z		A	В	С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

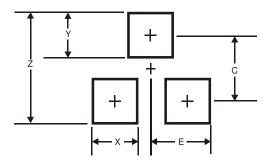


Mechanical Details



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
M	0.085	0.18	0.11			
α	0°	8°	-			
All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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